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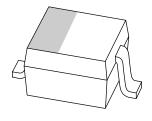
If you have any questions related to the data sheet, please contact our nearest sales office via e-mail or telephone (details via **salesaddresses@nexperia.com**). Thank you for your cooperation and understanding,

Kind regards,

Team Nexperia

# **DISCRETE SEMICONDUCTORS**

# DATA SHEET



# **PMEG2010EA**Low V<sub>F</sub> (MEGA) Schottky barrier diode

Product data sheet Supersedes data of 2002 Dec 10 2004 Feb 06



# Low V<sub>F</sub> (MEGA) Schottky barrier diode

# PMEG2010EA

### **FEATURES**

Forward current: 1 AReverse voltage: 20 V

Ultra high-speed switching

· Very low forward voltage

• Very small plastic SMD package.

### **APPLICATIONS**

• Ultra high-speed switching

· Voltage clamping

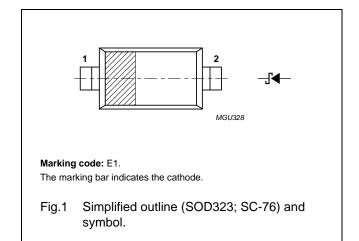
· Protection circuits.

# **DESCRIPTION**

Planar Maximum Efficiency General Application (MEGA) Schottky barrier diode with an integrated guard ring for stress protection, encapsulated in a SOD323 (SC-76) very small SMD plastic package.

### **PINNING**

PIN	DESCRIPTION
1	cathode
2	anode



# **ORDERING INFORMATION**

TYPE		PACKAGE	
NUMBER	NAME	DESCRIPTION	VERSION
PMEG2010EA	_	plastic surface mounted package; 2 leads	SOD323

### **LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V <sub>R</sub>	continuous reverse voltage		_	20	V
I <sub>F</sub>	continuous forward current		_	1	Α
I <sub>FSM</sub>	non-repetitive peak forward current	t <sub>p</sub> = 8.3 ms half sinewave; JEDEC method	_	5	А
T <sub>stg</sub>	storage temperature		-65	+150	°C
T <sub>j</sub>	junction temperature		_	125	°C
T <sub>amb</sub>	operating ambient temperature		-65	+125	°C

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# Low V<sub>F</sub> (MEGA) Schottky barrier diode

PMEG2010EA

# **CHARACTERISTICS**

 $T_{amb}$  = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	TYP.	MAX.	UNIT
V <sub>F</sub>	continuous forward voltage	see Fig.2; note 1			
		I <sub>F</sub> = 10 mA	240	270	mV
		I <sub>F</sub> = 100 mA	300	350	mV
		I <sub>F</sub> = 1000 mA	480	550	mV
I <sub>R</sub>	continuous reverse current	see Fig.3; note 1			
		V <sub>R</sub> = 5 V	5	10	μΑ
		V <sub>R</sub> = 8 V	7	20	μΑ
		V <sub>R</sub> = 15 V	10	50	μΑ
C <sub>d</sub>	diode capacitance	$V_R = 5 \text{ V}$ ; $f = 1 \text{ MHz}$ ; see Fig.4	19	25	pF

# Note

1. Pulsed test:  $t_p$  = 300  $\mu$ s;  $\delta$  = 0.02.

# THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	note 1	220	K/W
		note 2	180	K/W

# **Notes**

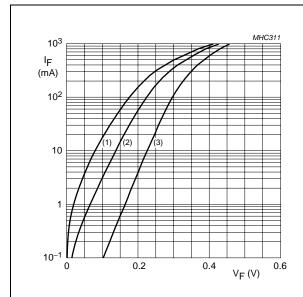
- 1. Device mounted on an FR4 printed-circuit board with Cu clad 10 x 10 mm.
- 2. Device mounted on an FR4 printed-circuit board with Cu clad 40 x 40 mm.

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# Low V<sub>F</sub> (MEGA) Schottky barrier diode

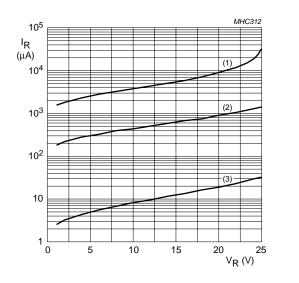
# PMEG2010EA

# **GRAPHICAL DATA**



- (1)  $T_{amb} = 125 \, ^{\circ}C$ .
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

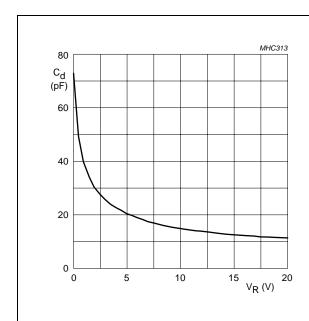
Fig.2 Forward current as a function of forward voltage; typical values.



- (1)  $T_{amb} = 125 \, ^{\circ}C.$
- (2)  $T_{amb} = 85 \, ^{\circ}C$ .
- (3)  $T_{amb} = 25 \, ^{\circ}C$ .

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Fig.3 Reverse current as a function of reverse voltage; typical values.



 $T_{amb} = 25 \, ^{\circ}C; f = 1 \, MHz.$ 

Fig.4 Diode capacitance as a function of reverse voltage; typical values.

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# Low V<sub>F</sub> (MEGA) Schottky barrier diode

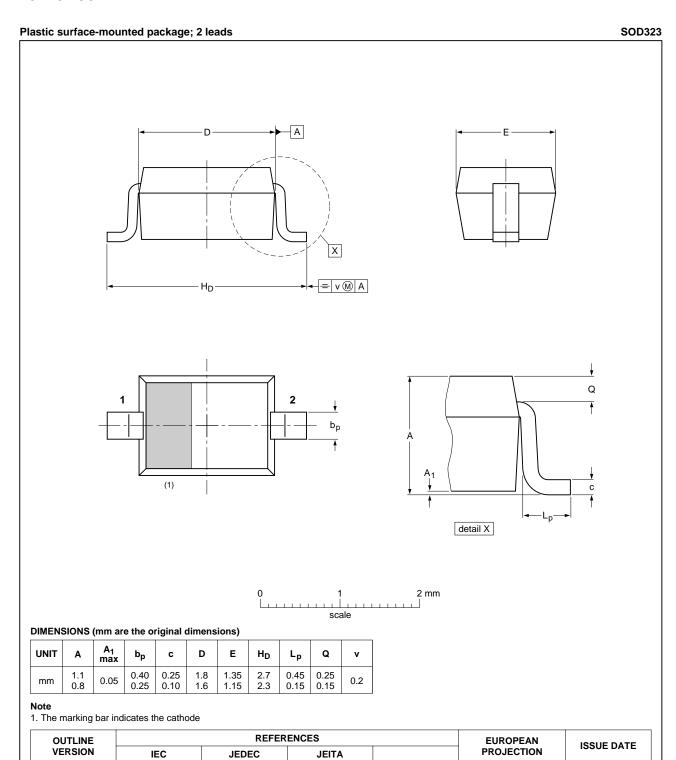
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03-12-17

06-03-16

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# **PACKAGE OUTLINE**



SC-76

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SOD323

# Low V<sub>F</sub> (MEGA) Schottky barrier diode

# PMEG2010EA

### **DATA SHEET STATUS**

DOCUMENT STATUS <sup>(1)</sup>	PRODUCT STATUS <sup>(2)</sup>	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

### Notes

- 1. Please consult the most recently issued document before initiating or completing a design.
- 2. The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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# **NXP Semiconductors**

# **Customer notification**

This data sheet was changed to reflect the new company name NXP Semiconductors, including new legal definitions and disclaimers. No changes were made to the technical content, except for package outline drawings which were updated to the latest version.

### **Contact information**

For additional information please visit: http://www.nxp.com
For sales offices addresses send e-mail to: salesaddresses@nxp.com

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